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				U.S. PATENT	DOCUMENTS					
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EXAMINER'S INITIALS	CITE NO.	Numl	per-Kind Code2 (# known)	MM-DD-YYYY	Document		Figures Appear			
-025	A1	US	2002/0172073	11/21/2002	HIDAKA		- not considered			
-CG		US	10/327,888	12/26/2002	HIDAKA		- 101		117/04	
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ap	-		SCHEUERLEIN, et al. "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in Each Cell" IEEE International Solid-State Circuits Conference (2000) TA 7.2							
ap	DURLAM, et al. "Nonvolatile RAM Based on Magnetic Tunnel Junction Elements" IEEE International Solid-State Circuits  Conference (2000) TA 7.3									
ap	NAJI, et al. "A 256kb 3.0V 1T1MJT Nonvolatile Magnetoresistive RAM" IEEE International Solid-State Circuits Conference (2001) TA 7.6								~	
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1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.